

N-Channel Enhancement Mode Power MOSFET

MTN4N65F3

BV_{DSS} : 650V
 $R_{DS(ON)}$: 3Ω (typ.)
 I_D : 4A

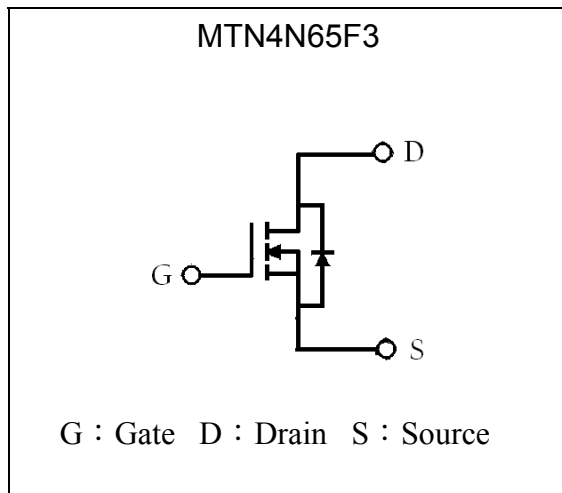
Features

- Low On Resistance
- Simple Drive Requirement
- Fast Switching Characteristic
- Pb-free lead plating and RoHS compliant package

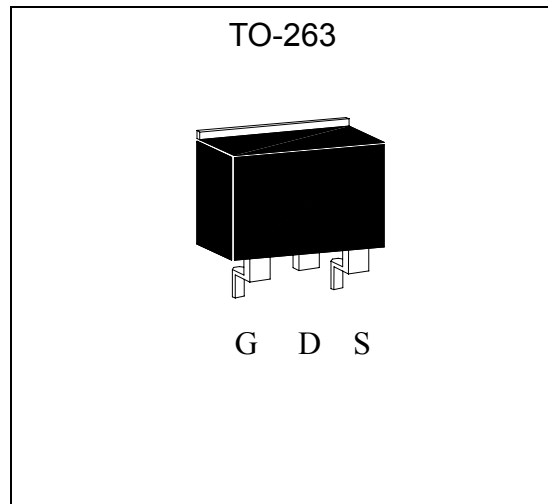
Applications

- Adapter
- Switching Mode Power Supply

Symbol

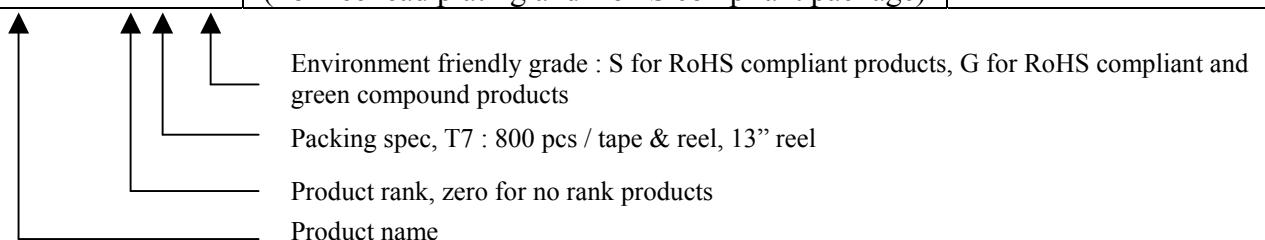


Outline



Ordering Information

Device	Package	Shipping
MTN4N65F3-0-T7-S	TO-263 (Pb-free lead plating and RoHS compliant package)	800 pcs / Tape & Reel



**Absolute Maximum Ratings** ($T_C=25^{\circ}\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	4*	A
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$	I_D	2.4*	A
Pulsed Drain Current @ $V_{GS}=10\text{V}$ (Note 1)	I_{DM}	16*	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	69	mJ
Avalanche Current (Note 1)	I_{AR}	4	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	3.4	mJ
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Maximum Temperature for Soldering @ Lead at 0.125 in(0.318mm) from case for 10 seconds	T_L	300	$^{\circ}\text{C}$
Total Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	100	W
Linear Derating Factor		0.8	W/ $^{\circ}\text{C}$
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^{\circ}\text{C}$

*Drain current limited by maximum junction temperature

Note : 1.Repetitive rating; pulse width limited by maximum junction temperature.

2. $I_{AS}=4\text{A}$, $V_{DD}=50\text{V}$, $L=8\text{mH}$, $R_G=25\Omega$, starting $T_J=+25^{\circ}\text{C}$.3. $I_{SD}\leq 4\text{A}$, $dI/dt\leq 100\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, starting $T_J=+25^{\circ}\text{C}$.**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1.25	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5	$^{\circ}\text{C}/\text{W}$



Characteristics (Tj=25°C, unless otherwise specified)

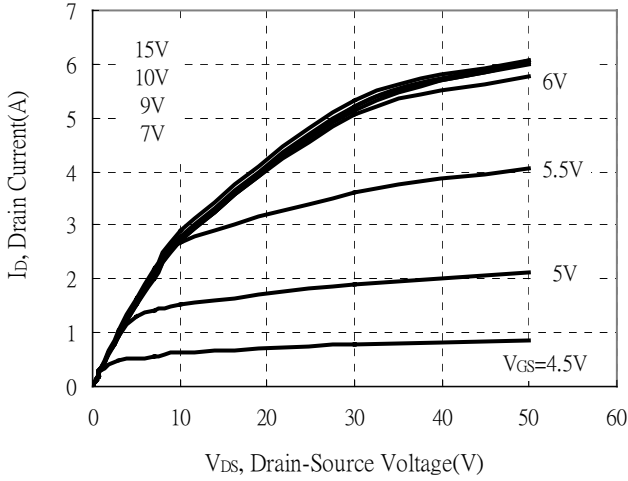
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	650	-	-	V	V _{GS} =0, I _D =250μA, Tj=25°C
ΔBV _{DSS} /ΔTj	-	0.5	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	2.3	-	S	V _{DS} =15V, I _D =2A
I _{GSS}	-	-	±100	nA	V _{GS} =±30
I _{DSS}	-	-	1	μA	V _{DS} =650V, V _{GS} =0
	-	-	10	μA	V _{DS} =520V, V _{GS} =0, T _C =125°C
*R _{DS(ON)}	-	3.0	3.5	Ω	V _{GS} =10V, I _D =2A
Dynamic					
*Q _g	-	11	-	nC	I _D =4A, V _{DD} =520V, V _{GS} =10V
*Q _{gs}	-	2.6	-		
*Q _{gd}	-	4.6	-		
*t _{d(ON)}	-	15	-	ns	V _{DD} =325V, I _D =4A, V _{GS} =10V, R _G =25Ω
*t _r	-	33	-		
*t _{d(OFF)}	-	30	-		
*t _f	-	37	-		
C _{iss}	-	568	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	51	-		
C _{rss}	-	9.6	-		
Source-Drain Diode					
*V _{SD}	-	-	1.5	V	I _S =4A, V _{GS} =0V
*I _S	-	-	4	A	
*I _{SM}	-	-	16		
*t _{rr}	-	280	-	ns	V _{GS} =0, I _F =4A, dI/dt=100A/μs
*Q _{rr}	-	2	-	μC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

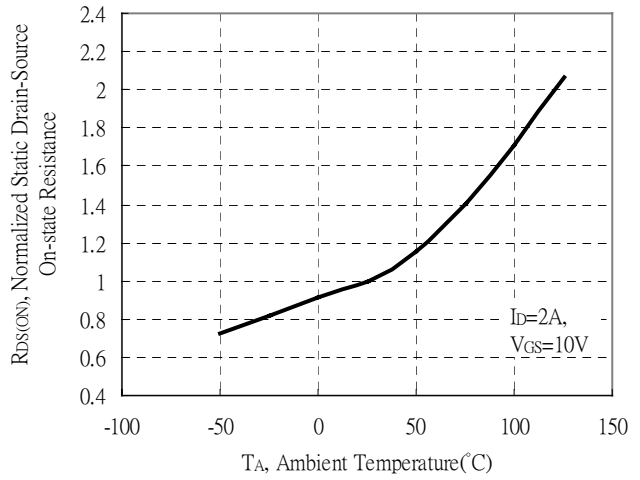


Typical Characteristics

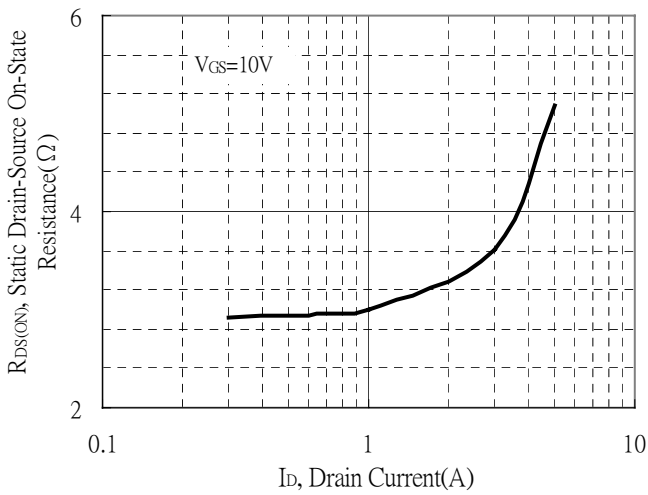
Typical Output Characteristics



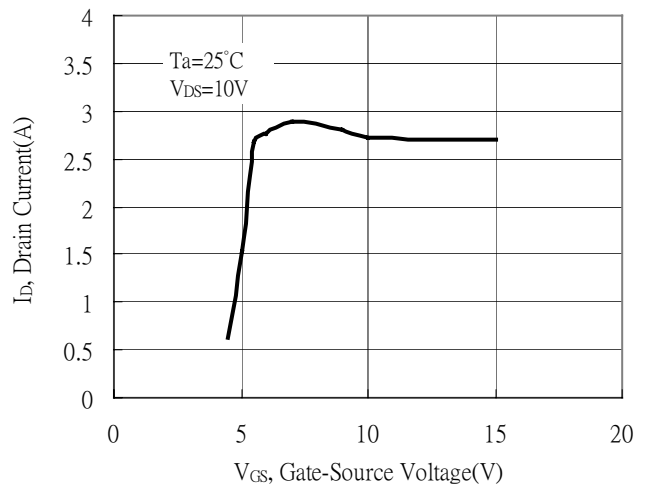
Static Drain-Source On-resistance vs Ambient Temperature



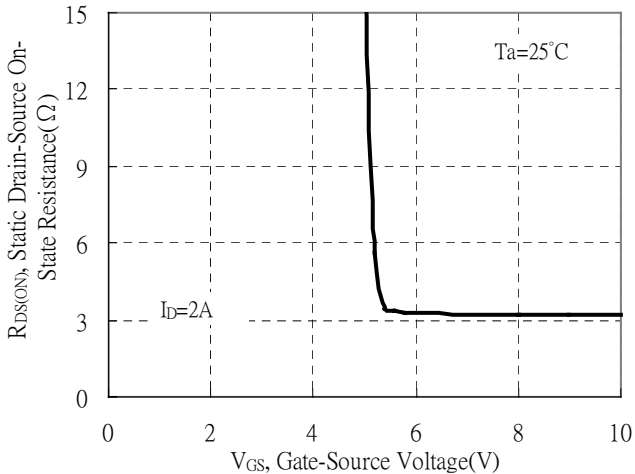
Static Drain-Source On-State resistance vs Drain Current



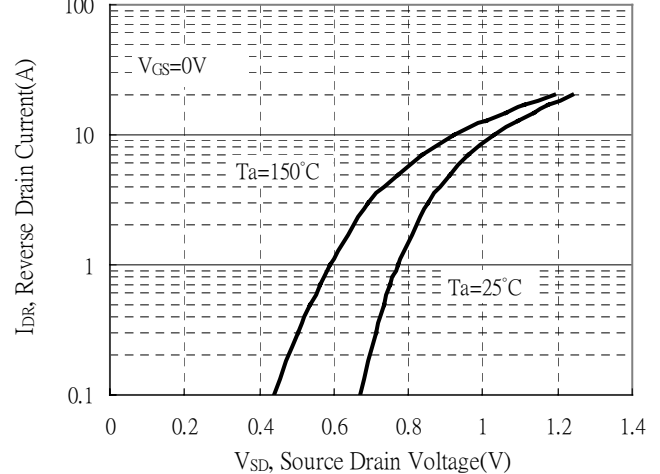
Drain Current vs Gate-Source Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage



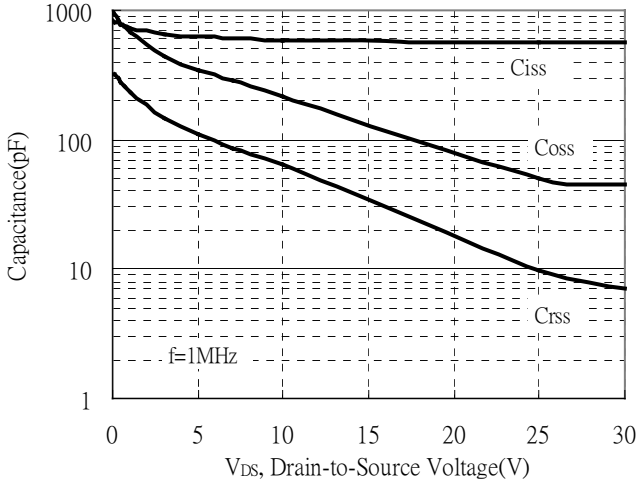
Body Diode Forward Voltage Variation with Source Current and Temperature



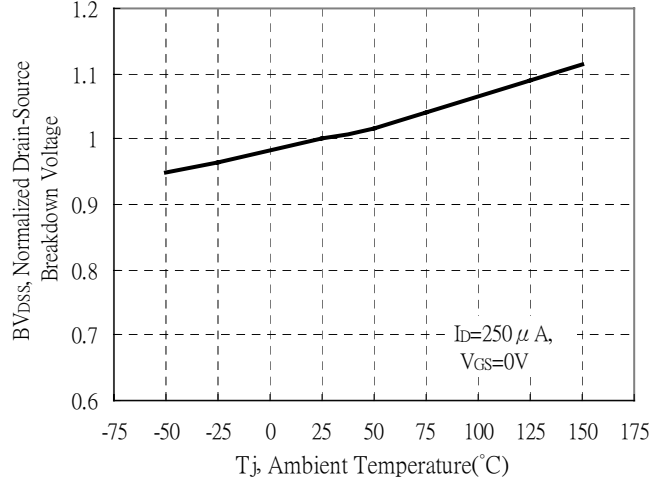


Typical Characteristics(Cont.)

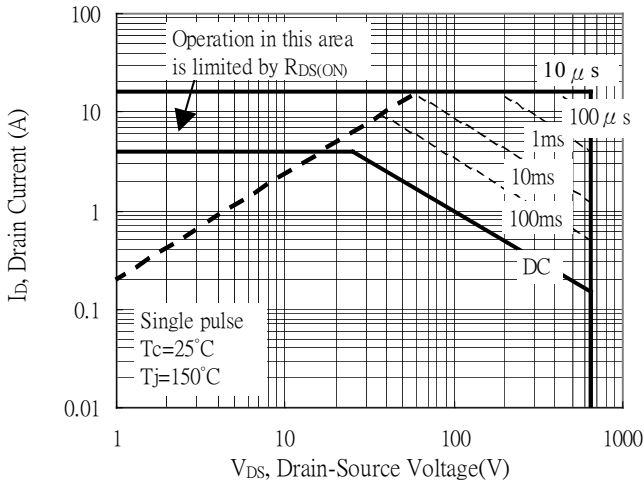
Capacitance vs Reverse Voltage



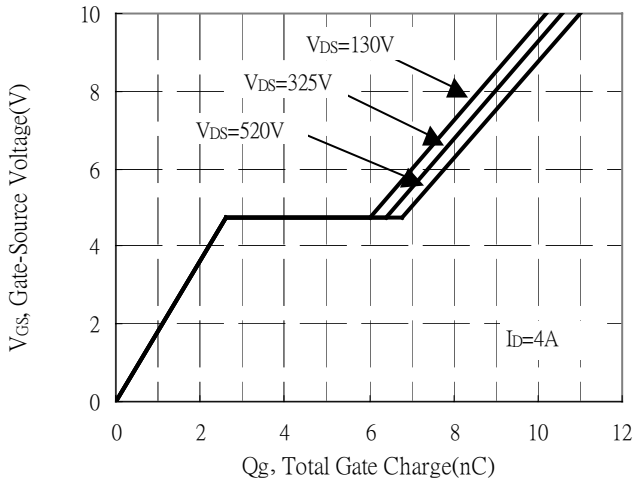
Brekdown Voltage vs Ambient Temperature



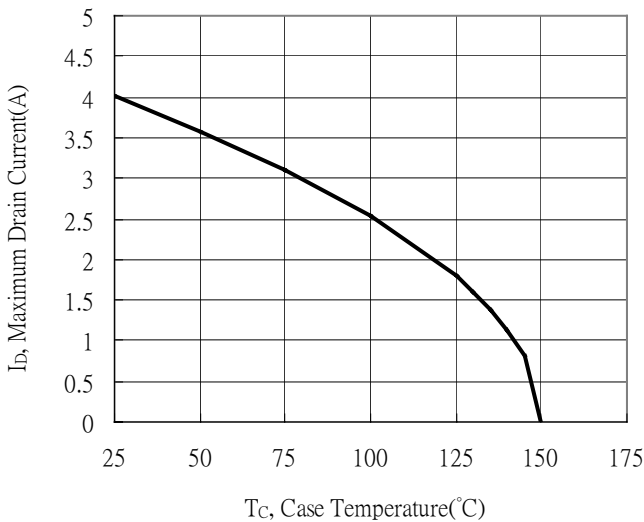
Maximum Safe Operating Area



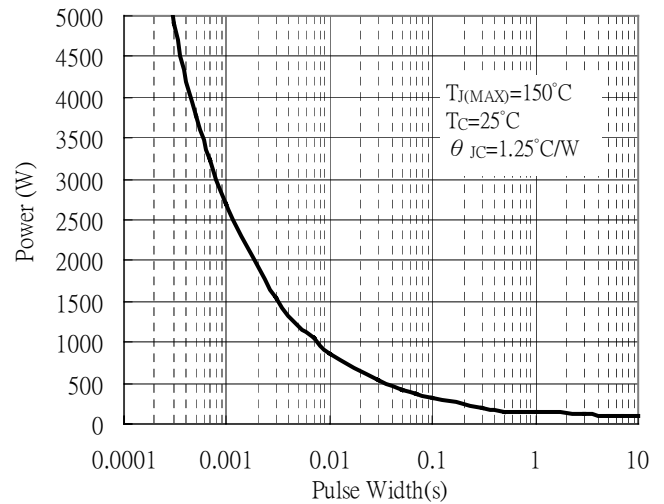
Gate Charge Characteristics



Maximum Drain Current vs Case Temperature

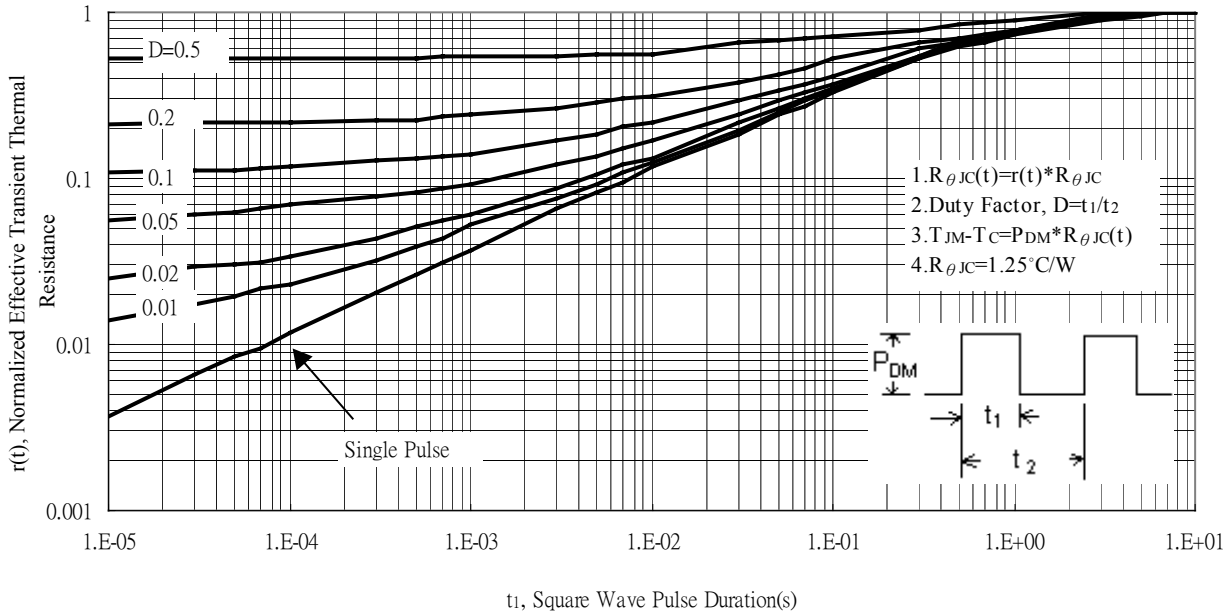


Single Pulse Power Rating, Junction to Case



Typical Characteristics(Cont.)

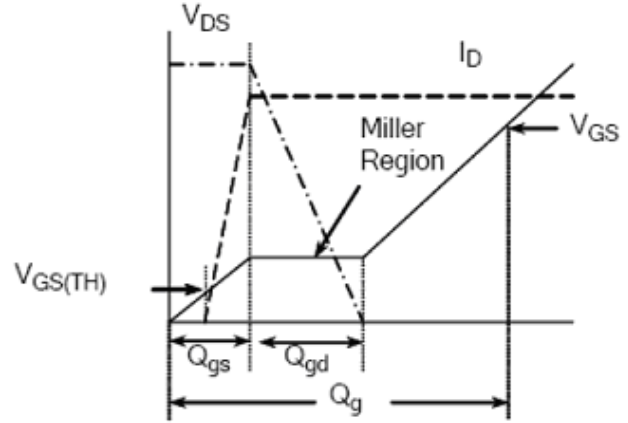
Transient Thermal Response Curves



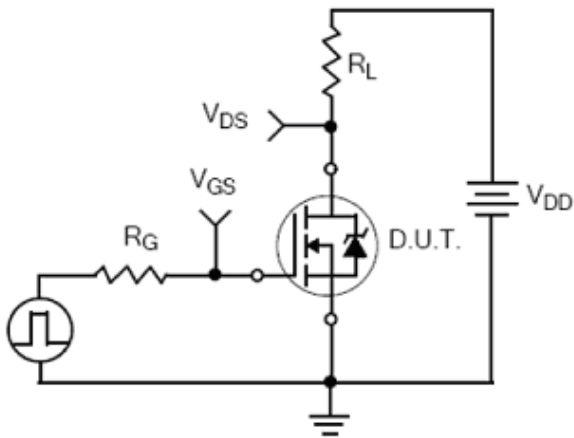
Test Circuit and Waveforms



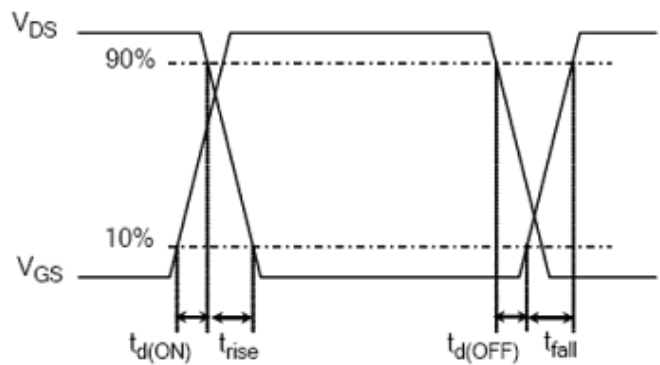
Gate Charge Test Circuit



Gate Charge Waveform



Resistive Switching Test Circuit



Resistive Switching Waveforms

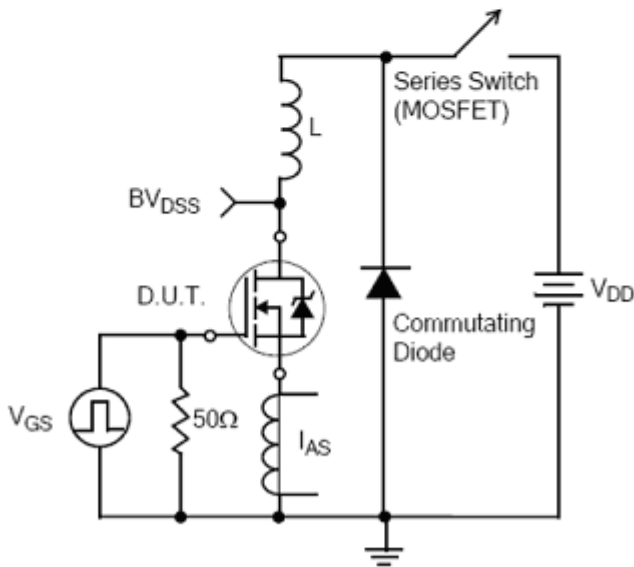
Test Circuit and Waveforms(Cont.)



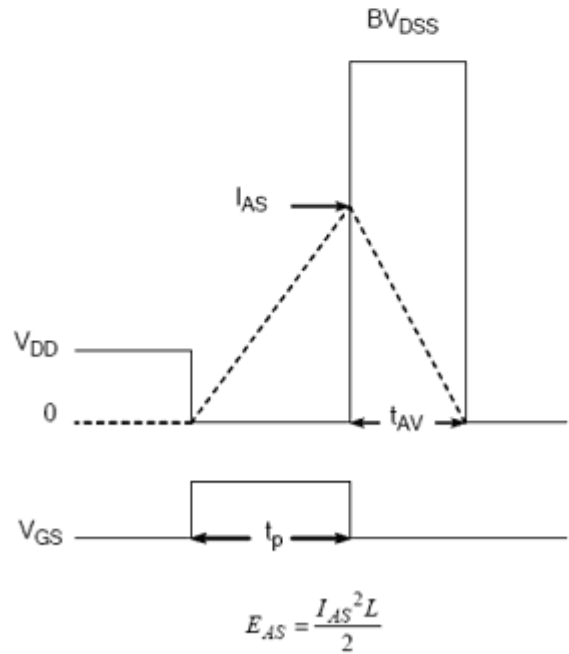
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform

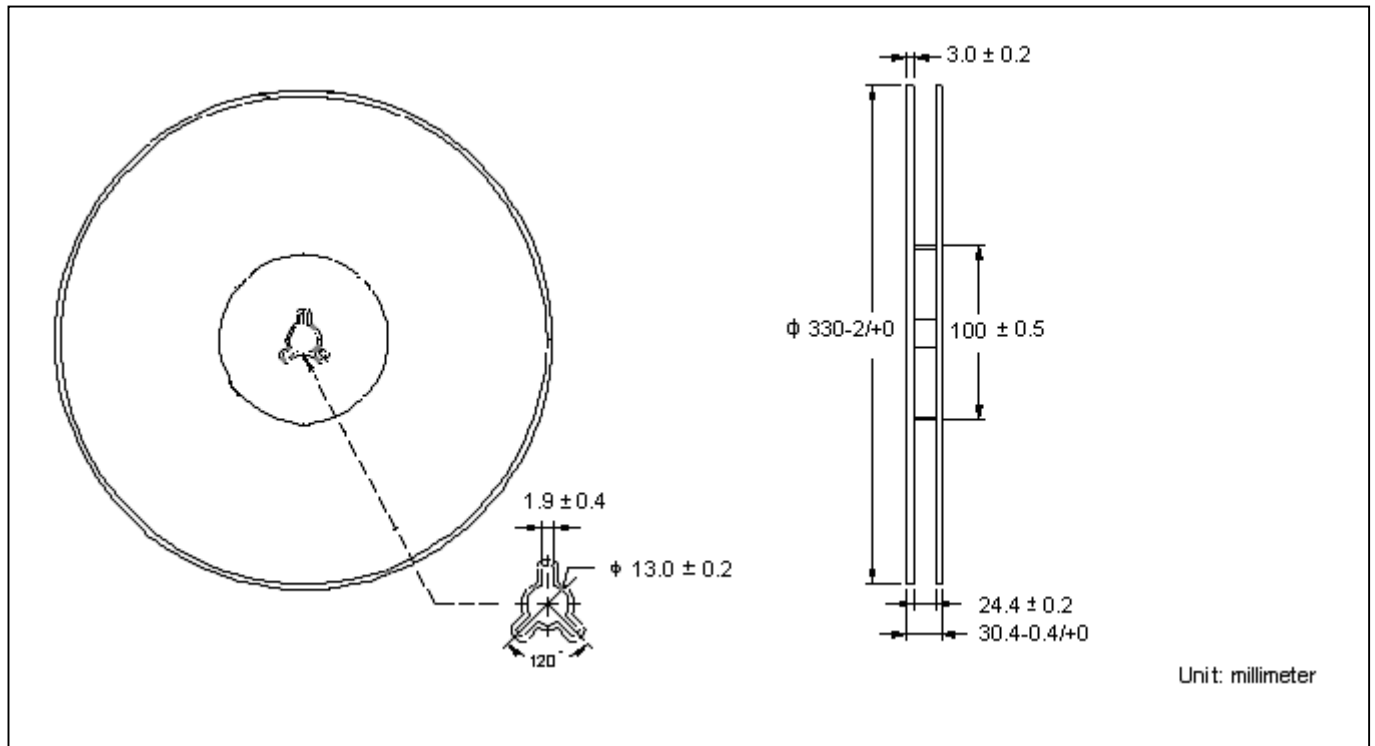


Unclamped Inductive Switching Test Circuit

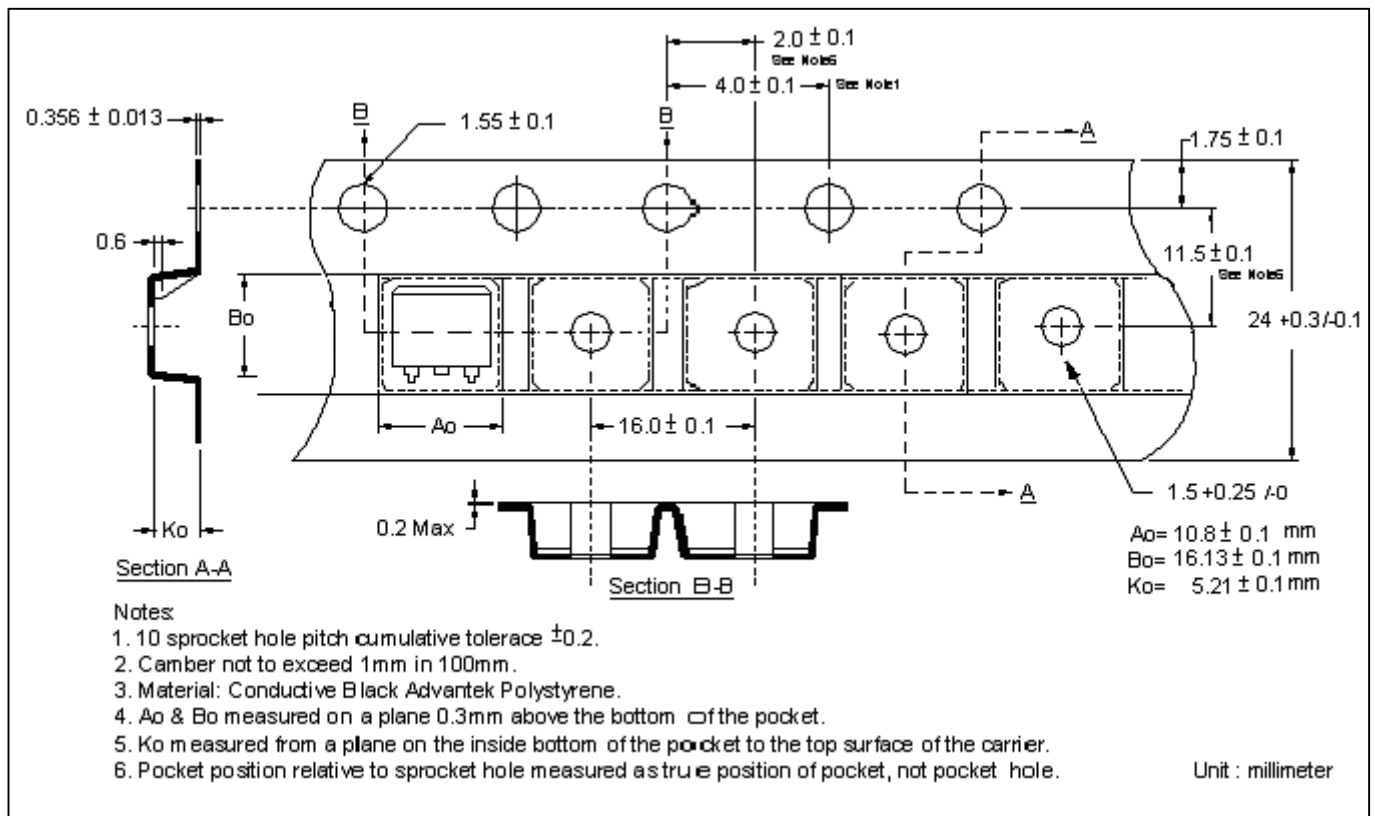


Unclamped Inductive Switching Waveforms

Reel Dimension

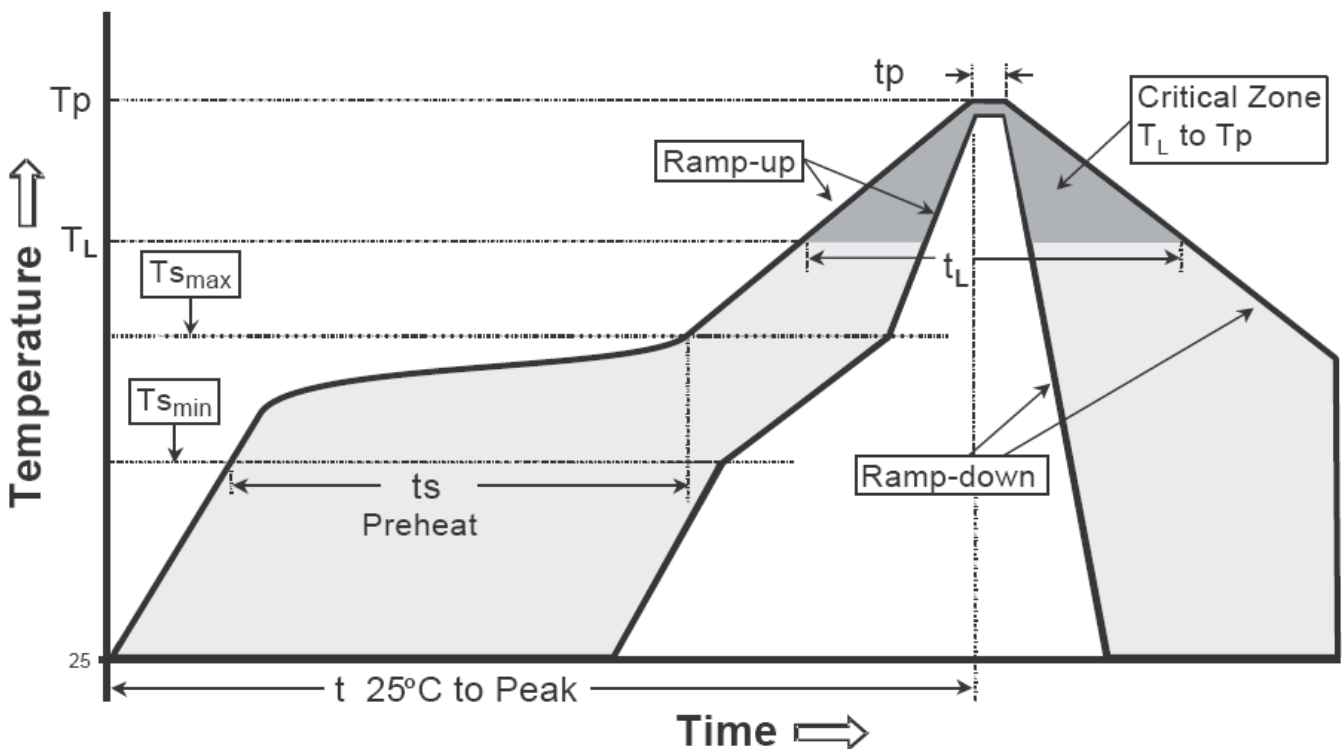


Carrier Tape Dimension



Recommended wave soldering condition

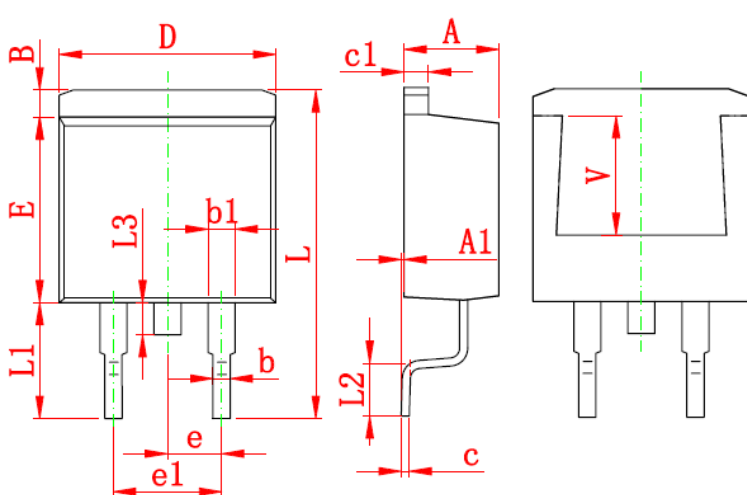
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

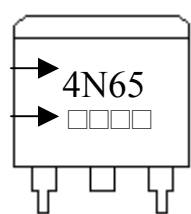
TO-263 Dimension



Marking :

Device Name → **4N65**

Date Code → □□□□



Style : Pin 1.Gate 2.Drain 3.Source

3-Lead Plastic Surface Mounted Package
 CYStek Package Code : F3

*:Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184	E	8.500	8.900	0.335	0.350
A1	0.000	0.150	0.000	0.006	e	*2.540		*0.100	
B	1.170	1.370	0.046	0.054	e1	4.980	5.180	0.196	0.204
b	0.710	0.910	0.028	0.036	L	15.050	15.450	0.593	0.608
b1	1.170	1.370	0.046	0.054	L1	5.080	5.480	0.200	0.216
c	0.310	0.530	0.012	0.021	L2	2.340	2.740	0.092	0.108
c1	1.170	1.370	0.046	0.054	L3	1.300	1.700	0.051	0.067
D	10.010	10.310	0.394	0.406	V	5.600	REF	0.220	REF

- Notes :**
- 1.Controlling dimension : millimeters.
 - 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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